



FZT688B

12V NPN MEDIUM POWER HIGH GAIN TRANSISTOR IN SOT223

Features

- BV_{CEO} > 12V
- BV_{CBO} > 12V
- I_C = 4A High Continuous Current
- h_{FE} > 400 @ 3A and Low Saturation Voltage
- Extremely Low Equivalent On-Resistance; RcE(sat) 83mΩ at 3A
- Complementary PNP Type: FZT788B
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT223
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (a)
- Weight: 0.112 grams (Approximate)

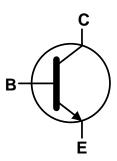
Applications

- Flash gun convertors
- · Battery powered circuits

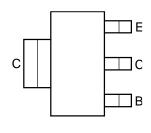
SOT223 (Type DN)



Top View



Device Symbol



Top View Pin-Out

Ordering Information (Note 4)

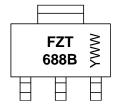
Part Number	Compliance	Package	Marking	Pool Size (inches)	Tape Width (mm)	Packing	
Fait Number	Compliance			Reel Size (Iliches)		Qty.	Carrier
FZT688BTA	Standard	SOT223 (Type DN)	FZT688B	7	12	1,000	Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

Marking Information

SOT223 (Type DN)



FZT 688B = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 2 = 2022) WW or $\overline{W}W$ = Week Code (01 to 53)



Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vcво	12	V
Collector-Emitter Voltage	VCEO	12	V
Emitter-Base Voltage	VEBO	7	V
Continuous Collector Current	Ic	4	Α
Peak Pulse Current	Ісм	10	Α

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)	6) Pp	3		
Power Dissipation	(Note 6)		2	W	
Power Dissipation	(Note 7)		1.6	VV	
	(Note 8)		1.2		
	(Note 5)		41.7		
Thermal Designation to Ambient	(Note 6)	Reja	62.5	7	
Thermal Resistance, Junction to Ambient	(Note 7)		78.1	°C/W	
	(Note 8)		104		
Thermal Resistance Junction to Lead (Note 9)		R ₀ JL	12.9		
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C		

ESD Ratings (Note 10)

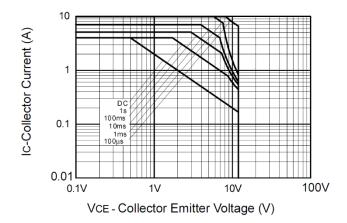
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:

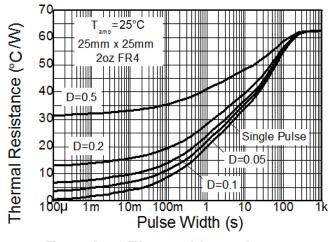
- For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
 Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
 Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 Same as Note 5, except the device is mounted on minimum recommended pad layout.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



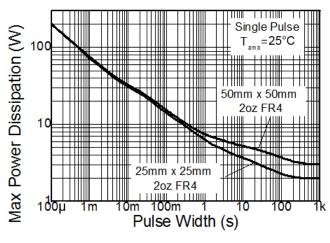
Thermal Characteristics and Derating Information



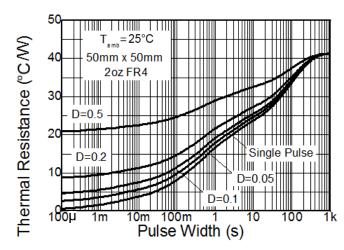
Safe Operating Area



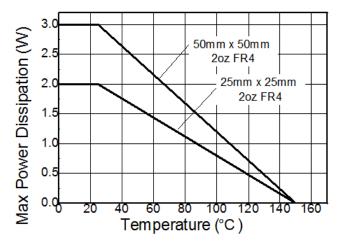
Transient Thermal Impedance



Pulse Power Dissipation



Transient Thermal Impedance



Derating Curve



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

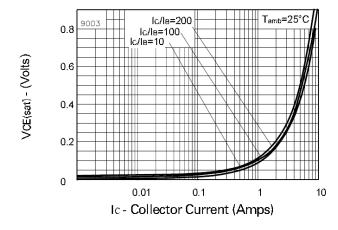
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	12	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 11)	BVceo	12	_	_	V	Ic = 10mA
Emitter-Base Breakdown Voltage	BV _{EBO}	7	_	_	V	I _E = 100μA
Collector-Base Cut-Off Current	I _{CBO}	_	_	20	nA	V _{CB} = 10V
Collector-Emitter Cut-Off Current	ICES	_	_	20	nA	V _{CE} = 10V
Emitter Cut-Off Current	I _{EBO}	_	_	20	nA	VEB = 6V
DC Current Gain (Note 11)	h _{FE}	500 400 100	_ _ _		_	Ic = 0.1A, Vce = 2V Ic = 3A, Vce = 2V Ic = 10A, Vce = 2V
Collector-Emitter Saturation Voltage (Note 11)	VCE(sat)	_ _ _ _ _	_ _ _ _ _	40 60 180 350 400	mV	IC = 0.1A, $IB = 1mAIC = 0.1A$, $IB = 0.5mAIC = 1A$, $IB = 50mAIC = 3A$, $IB = 20mAIC = 4A$, $IB = 50mA$
Base-Emitter Saturation Voltage (Note 11)	V _{BE(sat)}	_	_	1.1	V	Ic = 3A, I _B = 20mA
Base-Emitter Turn-On Voltage (Note 11)	V _{BE(on)}	_	_	1	V	Ic = 3A, Vce = 2V
Input Capacitance	Cibo	_	200	_	pF	V _{EB} = 0.5V, f = 1MHz
Output Capacitance	Cobo	_	40	_	pF	V _{CB} = 10V, f = 1MHz
Current Gain-Bandwidth Product	f⊤	150	_	_	MHz	V _{CE} = 5V, I _C = 50mA, f = 50MHz
Turn-On Time	ton	_	40		ns	Vcc = 10V, Ic = 500mA
Turn-Off Time	t _{off}	_	500		ns	$I_{B1} = -I_{B2} = 50 \text{mA}$

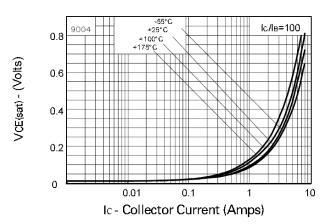
Note:

11. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



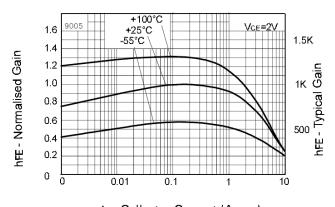
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

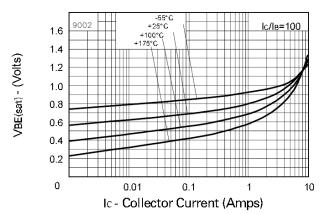




VCE(sat) v IC

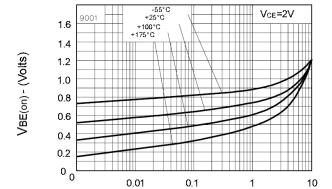
VCE(sat) v IC





Ic - Collector Current (Amps) **hFE v IC**

VBE(sat) v IC



Ic - Collector Current (Amps)

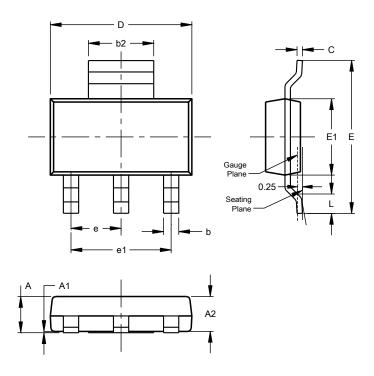
VBE(on) v IC



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

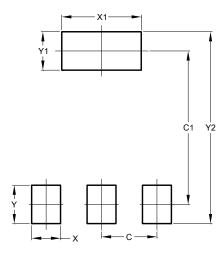


SOT223 (Type DN)					
Dim	Min	Max	Тур		
Α		1.70			
A1	0.01	0.15			
A2	1.50	1.68	1.60		
b	0.60	0.80	0.70		
b2	2.90	3.10			
C	0.20	0.32			
D	6.30	6.70			
Е	6.70	7.30			
E1	3.30	3.70			
е			2.30		
e1			4.60		
L	0.85				
All Dimensions in mm					

Suggested Pad Layout

 $\label{prop:lease} Please see \ http://www.diodes.com/package-outlines.html for the latest version.$

SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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